

查询"SK15GH063_06"供应商



SEMITOP® 2

IGBT Module

SK15GH063

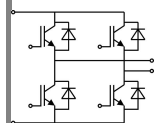
Preliminary Data

Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- N channel, homogeneous Silicon structure (NPT-Non punchthrough IGBT)
- High short circuit capability
- Low tail current with low temperature dependence
- UL recognized, file no. E63 532

Typical Applications

- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS



GH

Absolute Maximum Ratings			T _s = 25 °C, unless otherwise specified	
Symbol	Conditions		Values	Units
IGBT				
V _{CES}	T _j = 25 °C		600	V
I _C	T _j = 125 °C	T _s = 25 °C	20	A
		T _s = 80 °C	14	A
I _{CRM}	I _{CRM} = 2 x I _{Cnom}		30	A
V _{GES}			± 20	V
t _{psc}	V _{CC} = 300 V; V _{GE} ≤ 20 V; T _j = 125 °C V _{CES} < 600 V		10	µs
Inverse Diode				
I _F	T _j = 150 °C	T _s = 25 °C	20	A
		T _s = 80 °C	15	A
I _{FRM}	I _{FRM} = 2 x I _{Fnom}		28	A
I _{FSM}	t _p = 10 ms; half sine wave T _j = 150 °C		100	A
Module				
I _{t(RMS)}				A
T _{vj}			-40 ... +150	°C
T _{stg}			-40 ... +125	°C
V _{isol}	AC, 1 min.		2500	V

Characteristics			T _s = 25 °C, unless otherwise specified			
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 0,4 mA		4,5	5,5	6,5	V
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES} T _j = 25 °C T _j = 125 °C				0,05	mA mA
I _{GES}	V _{CE} = 0 V, V _{GE} = 20 V T _j = 25 °C T _j = 125 °C				120	nA nA
V _{CE0}				1,2 1		V V
r _{CE}	V _{GE} = 15 V T _j = 25°C T _j = 125°C			53		mΩ mΩ
V _{CE(sat)}	I _{Cnom} = 15 A, V _{GE} = 15 V T _j = 25°C _{chiplev.} T _j = 125°C _{chiplev.}			2	2,5	V V
C _{ies} C _{oes} C _{res}	V _{CE} = 25, V _{GE} = 0 V f = 1 MHz			0,8 0,06		nF nF nF
t _{d(on)} t _r E _{on}	R _{Gon} = 68 Ω	V _{CC} = 300V I _{Cnom} = 15A		35 50 0,71		ns ns mJ
t _{d(off)} t _f E _{off}	R _{Goff} = 68 Ω	T _j = 125 °C V _{GE} =±15V		250 20 0,4		ns ns mJ
R _{th(j-s)}	per IGBT				1,9	K/W



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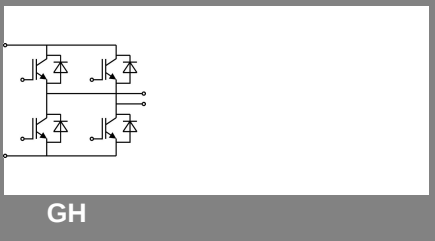
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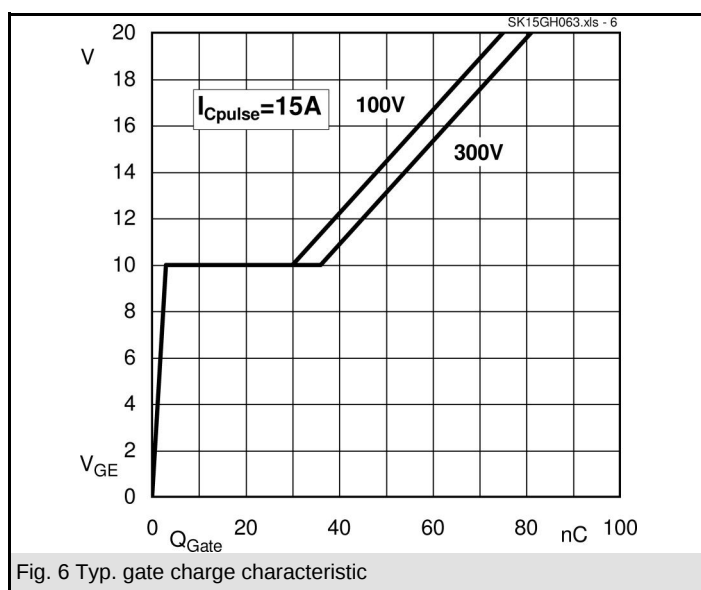
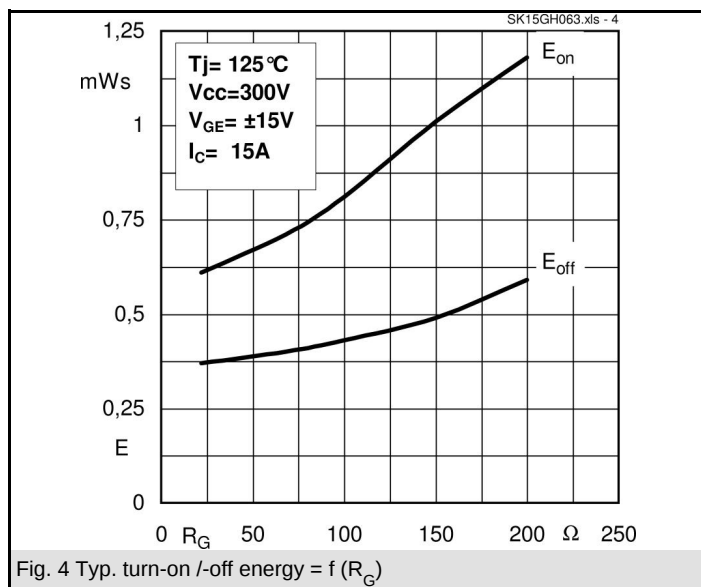
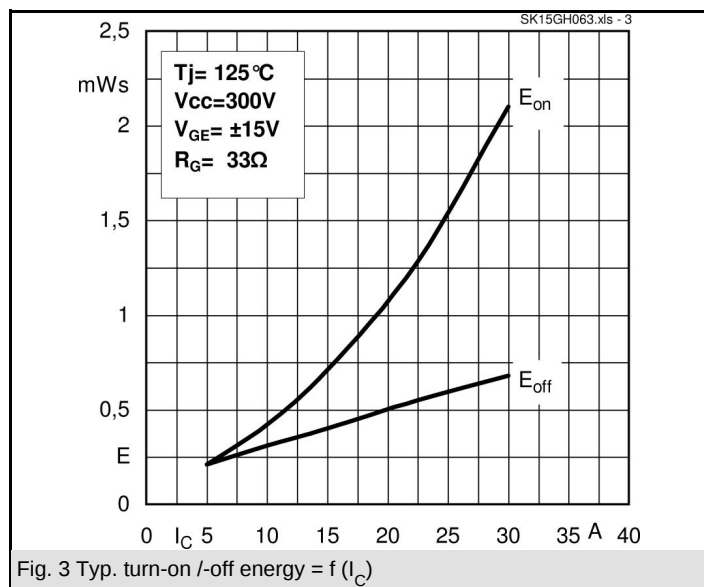
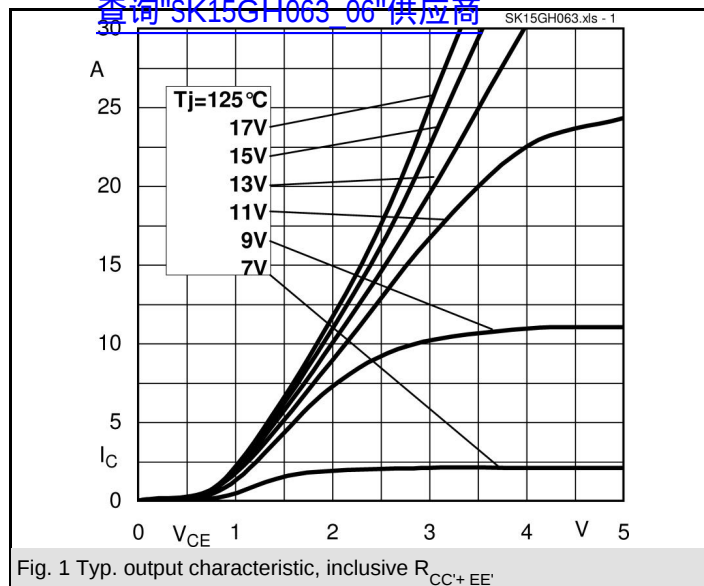


Characteristics						
Symbol	Conditions		min.	typ.	max.	Units
Inverse Diode						
V _F = V _{EC}	I _{Fnom} = 10 A; V _{GE} = 0 V	T _j = 25 °C _{chiplev.}		1,45	1,7	V
		T _j = 125 °C _{chiplev.}		1,4	1,7	V
V _{F0}		T _j = 125 °C		0,85	0,9	V
r _F		T _j = 125 °C		55	80	mΩ
I _{RRM}	I _{Fnom} = 10 A di/dt = -200 A/μs V _{CC} = 300V	T _j = 125 °C		13		A
Q _{rr}				1,5		μC
E _{rr}				0,45		mJ
R _{th(j-s)D}	per diode				1,2	K/W
M _s	to heat sink M1				2	Nm
w				19		g

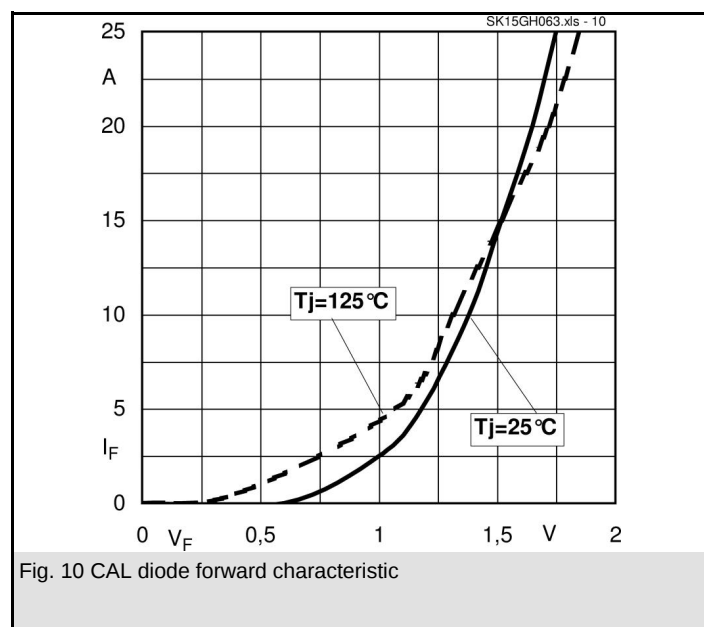
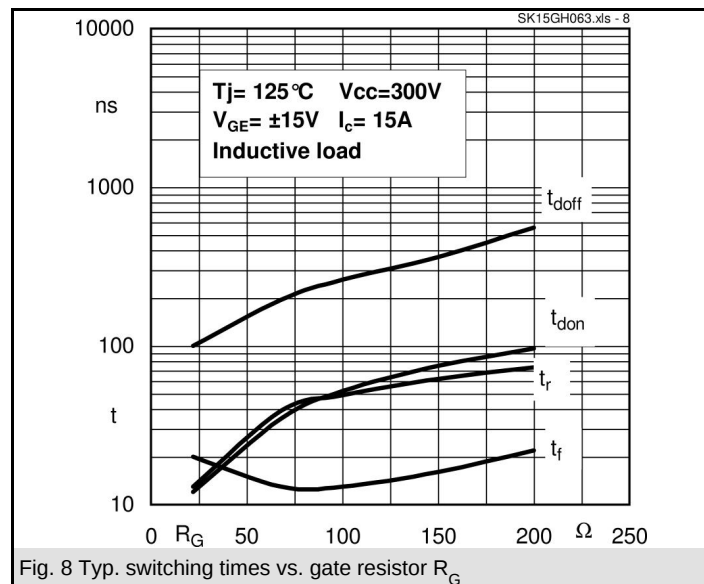
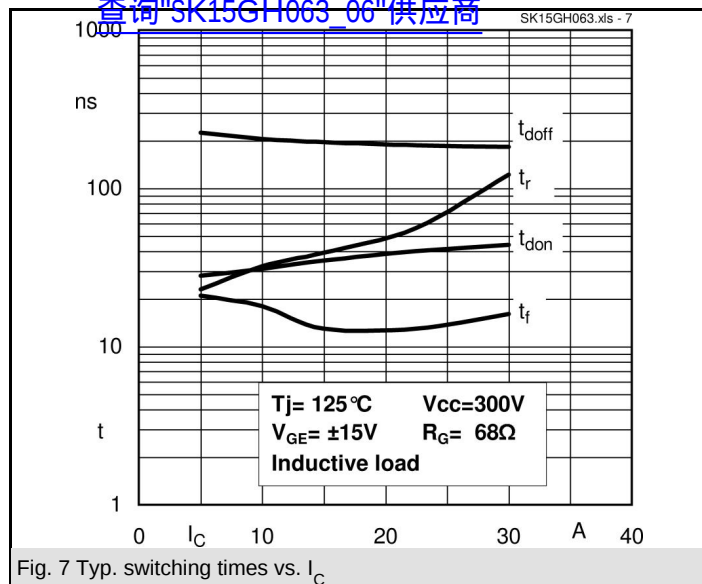
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

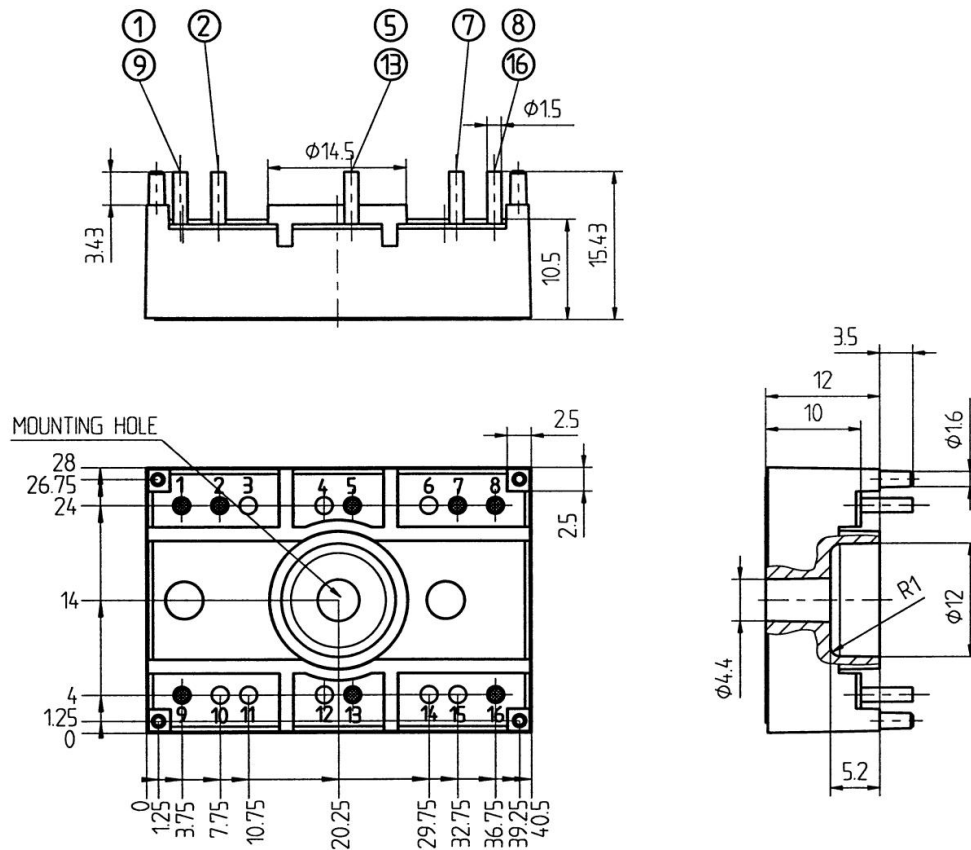
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Case T5 (Suggested hole diameter, in the PCB, for solder pins and plastic mounting pins: 2mm)

